

isc Silicon NPN Power Transistor

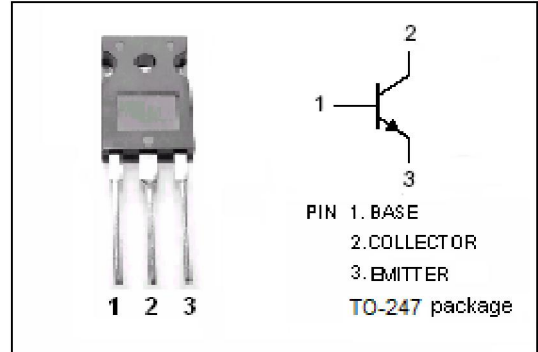
BUW11W

DESCRIPTION

- High Voltage
- High Speed Switching

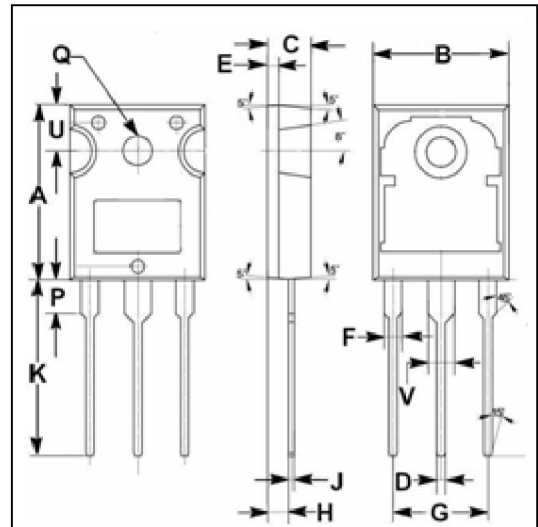
APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor control systems



ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-Base Voltage	850	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current-Continuous	5	A
I _{CM}	Collector Current-Peak	10	A
I _B	Base Current	2	A
I _{BM}	Base Current-Peak	4	A
P _C	Collector Power Dissipation @T _c =25°C	100	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C



DIM	mm	
	MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.25	°C/W

isc Silicon NPN Power Transistor**BUW11W****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.1\text{A}; I_B=0, L=25\text{mH}$	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.6\text{A}$			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.6\text{A}$			1.4	V
I_{CES}	Collector Cutoff Current	$V_{CE}=\text{Rated } V_{CES}; V_{BE}=0$ $V_{CE}=\text{Rated } V_{CES}; V_{BE}=0; T_C=125^{\circ}\text{C}$			1.0 2.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=9\text{V}; I_C=0$			10	mA
h_{FE-1}	DC Current Gain	$I_C=5\text{mA}; V_{CE}=5\text{V}$	10		35	
h_{FE-2}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	10		35	

Switching Times ;Resistive Load

t_{on}	Turn-on Time	$I_C=3\text{A}; I_{B1}=-I_{B2}=0.6\text{A}$			1.0	μs
t_s	Storage Time				4.0	μs
t_f	Fall Time				0.8	μs